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June 2016

## FDC021N30

# N-Channel PowerTrench® MOSFET 30 V, 6.1 A, 26 m $\Omega$

#### **Features**

- Max  $r_{DS(on)} = 26 \text{ m}\Omega$  at  $V_{GS} = 10 \text{ V}$ ,  $I_D = 6.1 \text{ A}$
- Max  $r_{DS(on)} = 33 \text{ m}\Omega$  at  $V_{GS} = 4.5 \text{ V}$ ,  $I_D = 5.3 \text{ A}$
- High Performance Trench Technology for Extremely Low rDS(on)
- High Power and Current Handling Capability in a Widely Used Surface Mount Package
- Fast Switching Speed
- RoHS Compliant

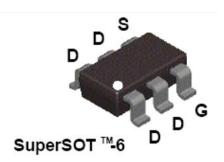


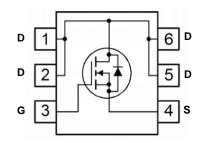
## **General Description**

This N-Channel PowerTrench MOSFET is produced using Fairchild's advanced PowerTrench® process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

## **Applications**

- Load Switch
- Battery Protection
- Power Management





## **MOSFET Maximum Ratings** T<sub>A</sub>= 25°C unless otherwise noted.

Symbol	Parameter	Ratings	Units		
V <sub>DS</sub>	Drain to Source Voltage			30	V
V <sub>GS</sub>	Gate to Source Voltage		(Note 3)	±20	V
1	-Continuous	T <sub>A</sub> = 25°C	(Note 1a)	6.1	^
ID	-Pulsed		(Note 4)	62	A
D	Power Dissipation		(Note 1a)	1.6	W
$P_{D}$	Power Dissipation		(Note 1b)	0.7	VV
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature I	Range		-55 to + 150	°C

#### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	78	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	175	°C/W

### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
21N	FDC021N30	SSOT-6 <sup>TM</sup>	7 "	8 mm	3000 units

## **Electrical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Chara	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu A$ , referenced to 25°C		16		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V			1	μА
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V			100	nA

#### On Characteristics

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	1.0	1.8	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu A$ , referenced to 25°C		-5		mV/°C
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6.1 A		19	26	
r <sub>DS(on)</sub> Static Drain to Source On Resistance	Static Drain to Source On Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 5.3 \text{ A}$		23	33	mΩ
	$V_{GS} = 10 \text{ V, } I_D = 6.1 \text{ A,}$ $T_J = 125^{\circ}\text{C}$		26	37	- 11122	
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 6.1 A		30		S

### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 45.V.V 0.V		510	710	pF
Coss	Output Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$		170	240	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1 1/11/12		22	30	pF
R <sub>g</sub>	Gate Resistance		0.1	1.3	2.6	Ω

## **Switching Characteristics**

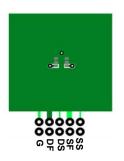
t <sub>d(on)</sub>	Turn-On Delay Time		6	12	ns
t <sub>r</sub>	Rise Time	V <sub>DD</sub> = 15 V, I <sub>D</sub> = 6.1 A,	2	10	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$	13	24	ns
t <sub>f</sub>	Fall Time		2	10	ns
$Q_{g(TOT)}$	Total Gate Charge	V <sub>GS</sub> = 0 V to 10 V	7.7	10.8	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0 \text{ V to } 4.5 \text{ V}$ $I_{D} = 15 \text{ V},$ $I_{D} = 6.1 \text{ A}$	3.7	5.2	nC
$Q_{gs}$	Gate to Source Charge	1 <sub>D</sub> =0.1 A	1.4		nC
$Q_{gd}$	Gate to Drain "Miller" Charge		1.1		nC

## **Drain-Source Diode Characteristics**

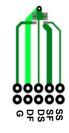
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V, } I_{S} = 6.1 \text{ A}$ (Note 2)		0.8	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	-I <sub>E</sub> = 6.1 A, di/dt = 100 A/μs		14	25	ns
Q <sub>rr</sub>	Reverse Recovery Charge	1 <sub>F</sub> = 6.1 A, α/αι = 100 A/μs		3	10	nC

#### Notes:

<sup>1:</sup> R<sub>0JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a. 78 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b.175 °C/W when mounted on a minimum pad of 2 oz copper

<sup>2:</sup> Pulse Test: Pulse Width<300 us, Duty Cycle<2.0%.
3. As an N-ch device, the negative Vgs rating is for low duty cycle pulse occurrence only. No continuous rating is implied.
4. Pulsed Id please refer to Fig 11 SOA graph for more details.

## **Typical Characteristics** $T_J = 25$ °C unless otherwise noted.

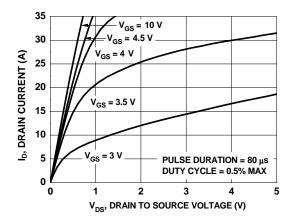


Figure 1. On-Region Characteristics

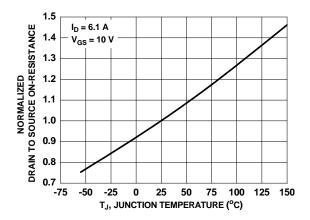


Figure 3. Normalized On-Resistance vs. Junction Temperature

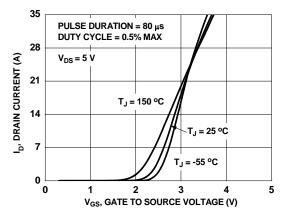


Figure 5. Transfer Characteristics

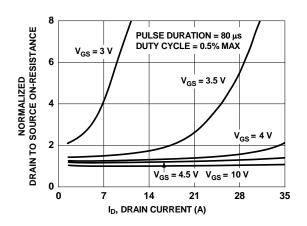


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

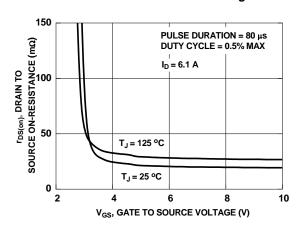


Figure 4. On-Resistance vs. Gate to Source Voltage

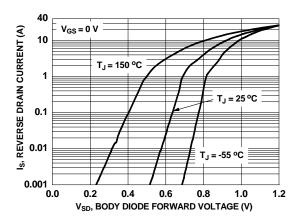


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

## **Typical Characteristics** $T_J = 25$ °C unless otherwise noted.

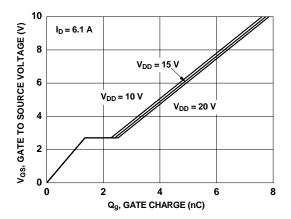


Figure 7. Gate Charge Characteristics

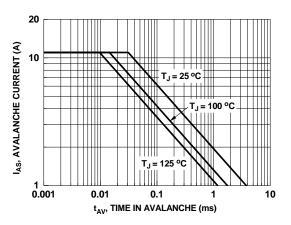


Figure 9. Unclamped Inductive Switching Capability

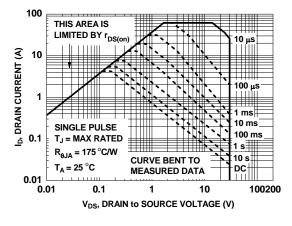


Figure 11. Forward Bias Safe Operating Area

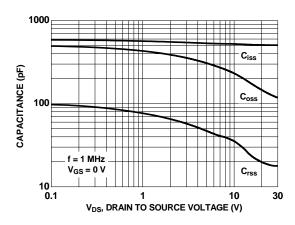


Figure 8. Capacitance vs. Drain to Source Voltage

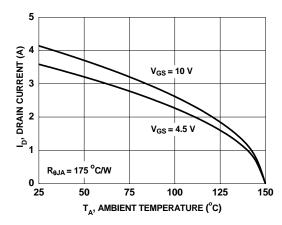


Figure 10. Maximum Continous Drain Current vs. Ambient Temperature

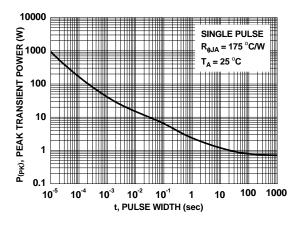


Figure 12. Single Pulse Maximum Power Dissipation

## **Typical Characteristics** $T_J = 25$ °C unless otherwise noted.

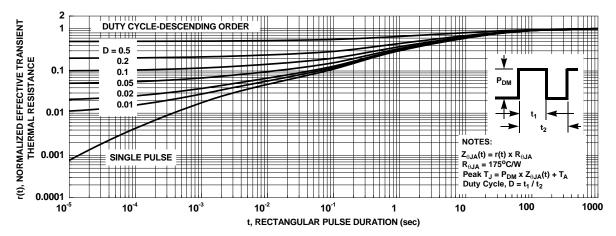
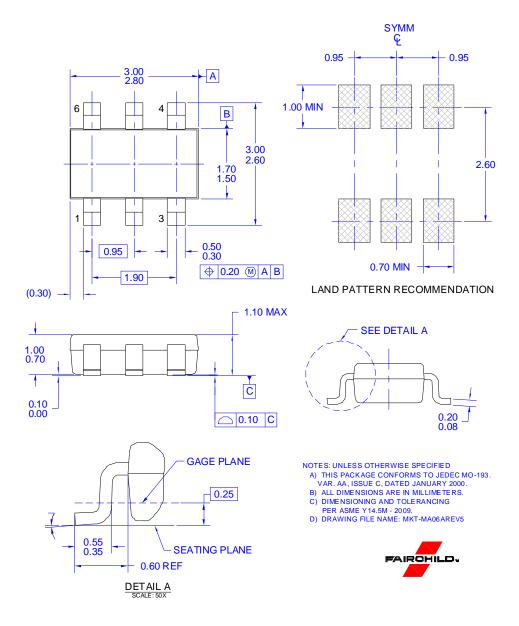


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

## **Dimensional Outline and Pad Layout**



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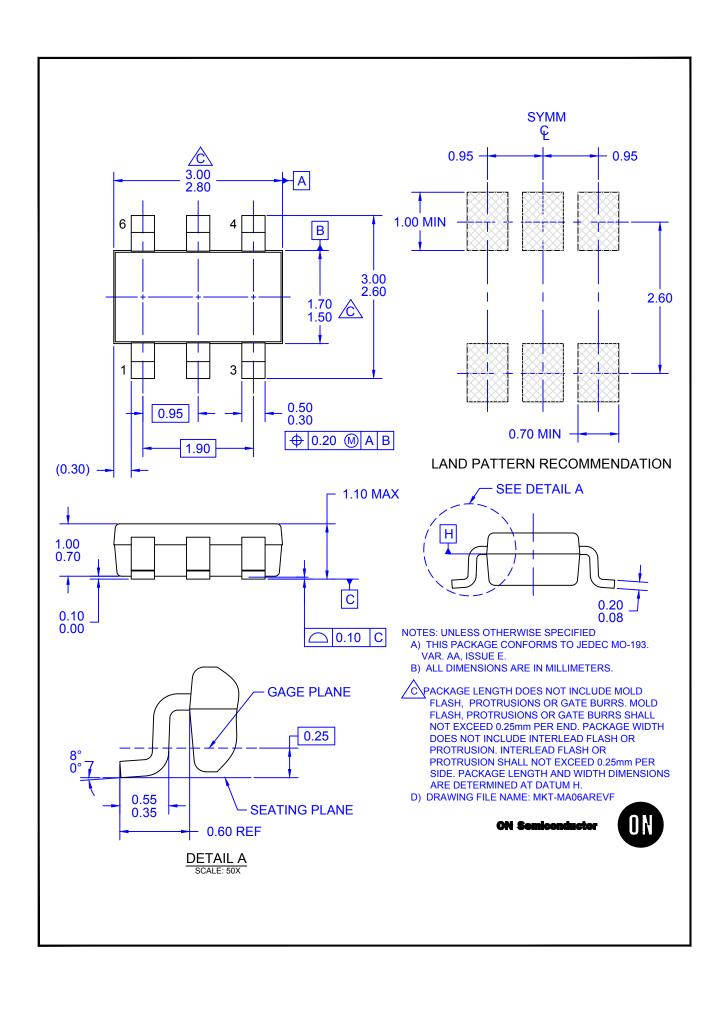
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